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(54) **MRAM REFILL DEVICE STRUCTURE**

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ABSTRACT

Embodiments of present invention provide a method of forming a MRAM structure. The method includes forming a dielectric layer on top of a bottom contact; creating an opening in the dielectric layer, the opening has a slant top edge; filling a bottom portion of the opening to form a bottom electrode; filling a top portion of the opening with a first ferromagnetic material to form a first ferromagnetic layer; forming a stack of blanket layers, including a blanket tunnel barrier layer, a blanket second ferromagnetic layer, and a blanket top electrode layer, on top of the first ferromagnetic layer; patterning the stack of blanket layers into a top portion of a magnetic tunnel junction stack that includes a tunnel barrier layer, a second ferromagnetic layer, and a top electrode; and forming a top contact in contact with the top electrode. A structure formed thereby is also provided.

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